

### **NPN BD131**

# SILICON PLANAR EPITAXIAL POWER TRANSISTORS

The BD131are NPN transistors mounted in Jedec TO-126 plastic package. Medium power applications. PNP complements are BD132 Compliance to RoHS.

## **ABSOLUTE MAXIMUM RATINGS**

Symbol	Ratings		Value	Unit	
V <sub>CEO</sub>	Collector-Emitter Voltage		45	V	
$V_{CBO}$	Collector-Base Voltage		45	V	
$V_{EBO}$	Emitter-Base Voltage		4	V	
I <sub>C</sub>	Collector Current	I <sub>C</sub>	3	Α	
		I <sub>CM</sub>	6	^	
	Base current (peak value)	I <sub>BM</sub>	0.5	А	
IB	Reverse base current (peak value)	I <sub>BM</sub>	0.5		
P <sub>T</sub>	Total power Dissipation	@ $T_{mb} = 60^{\circ}C$	15	W	
TJ	Junction Temperature		150	Ŝ	
T <sub>Stg</sub>	Storage Temperature		-65 to +150	°C	

#### THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit
$R_{thJ-mb}$	Thermal Resistance, Junction to mouting base	6	K/W

#### **ELECTRICAL CHARACTERISTICS**

TC=25°C unless otherwise noted

Symbol	Ratings	Test Condition(s)	Min	Тур	Max	Unit
	Collector cut-off current	$I_E=0$ , $V_{CB}=40$ V	-	-	5	
I <sub>CBO</sub>	Collector cut-on current	I <sub>E</sub> =0 , V <sub>CB</sub> =40 V , <b>T</b> <sub>i</sub> = 150°C	-	-	500	μA
I <sub>EBO</sub>	Emitter cut-offcurrent	I <sub>C</sub> =0, V <sub>EB</sub> =3 V	-	-	5	μΑ
V	Collector-Emitter saturation	I <sub>C</sub> =0.5 A, I <sub>B</sub> =50 mA	-	-	0.3	V
V <sub>CE(SAT)</sub>	Voltage	I <sub>C</sub> =2.0 A, I <sub>B</sub> =200 mA	-	-	1.2	V
V	Base-Emitter saturation	I <sub>C</sub> =0.5 A, I <sub>B</sub> =50 mA	-	-	0.7	V
V <sub>BE(SAT)</sub>	Voltage	I <sub>C</sub> =2.0 A, I <sub>B</sub> =200 mA	-	-	1,5	V
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> =12 V, I <sub>C</sub> =500m A	40	-	-	
		V <sub>CE</sub> =1 V, I <sub>C</sub> =2 A	20	-	-	

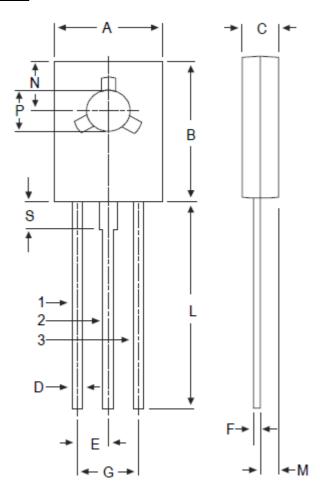


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#### **MECHANICAL DATA CASE TO-126**

	DIMENSIONS		
	min	max	
Α	7.4	7.8	
В	10.5	10.8	
С	2.4	2.7	
D	0.7	0.9	
Е	2.25 typ.		
F	0.49	0.75	
G	4.4 typ.		
L	15.7 typ.		
М	1.27 typ.		
N	3.75 typ.		
Р	3.0	3.2	
S	2.54 typ.		

Pin 1 :	Emitter
Pin 2 :	Collector
Pin 3 :	Base



#### Revised September 2012

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